BGA728L7

Broadband Low Noise Amplifier for Portable and Mobile TV Applications

Small Signal Discretes



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BGA728	3L7
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Page	Subjects (major changes since last revision)
All	Status changed from preliminary to final data sheet

Data Sheet 3 Rev. 2.0, 2009-01-20

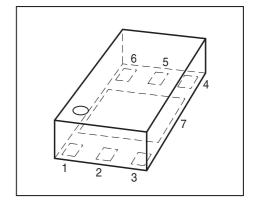


Broadband Low Noise Amplifier for Portable and Mobile TV Applications

1 Broadband Low Noise Amplifier for Portable and Mobile TV Applications

Features

- High gain mode: 15.75 dB gainLow gain mode: -5.2 dB gain
- Noise figure: 1.3 / 5.5 dB in high / low gain mode
- Power off function
- Operating frequency: 100 ~ 1700 MHz
- Supply voltage: 1.5 V to 3.6 V
- Small leadless TSLP-7-1 package (2.0 x 1.3 x 0.4 mm³)
- Output internally matched to 50 Ω
- Input pre-matched to 50 Ω
- Low external component count
- Integrated ESD protection (1 kV HBM)
- Moisture sensitivity level: MSL 1
- Pb-free (RoHS compliant) package



TSLP-7-1



Applications

- · Portable and mobile TV in VHFIII-, UHF- and L-bands
- ISM applications in 100... 1700 MHz
- · RKE applications

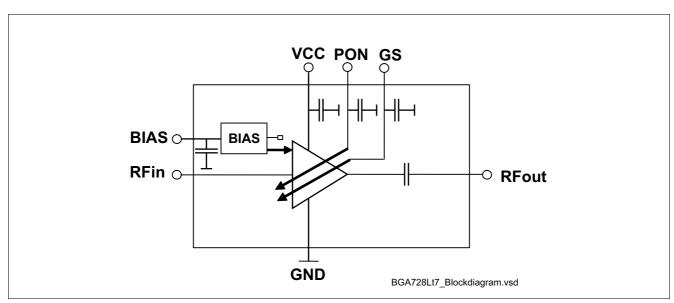


Figure 1 Block diagram



Description

2 Description

The BGA728L7 is a low power low noise amplifier (LNA) MMIC for portable and mobile TV applications in the VHFIII-, UHF- and L-Bands. The low gain mode with much higher linearity enables this LNA to work with much lower current consumption than commonly used TV LNAs. The LNA is based upon Infineon Technologies cost effective B7HFM Silicon Germanium technology and comes into a low profile TSLP-7-1 leadless green package. This document specifies the electrical parameters, pin-out, application circuit and packaging of the chip.

Туре	Package	Marking
BGA728L7	TSLP-7-1	AP

Pin Definition and Function

Table 1 Pin Definition and Function

Pin No.	Symbol	Function	
1	GS	High-gain / Low-gain control	
2	RFin	RF input	
3	BIAS	Bias voltage	
4	PON	Power on / off control	
5	RFout	RF output	
6	VCC	Supply voltage	
7	GND	DC/RF ground	

Maximum Ratings

Table 2 Maximum Ratings

Parameter ¹⁾	Symbol	Value	Unit
Voltage at pin VCC	$V_{\sf CC}$	-0.3 3.6	V
Voltage at pin RF_IN	V_{RFIN}	-0.3 0.9	V
Voltage at pin RF_OUT	V_{RFOUT}	-0.3 V _{CC} + 0.3	V
Voltage at pin PON	V_{PON}	-0.3 V _{CC} + 0.3	V
Current into pin VCC	I_{CC}	20	mA
RF input power	P_{IN}	10	dBm
Total power dissipation	P_{tot}	72	mW
Junction temperature	T_{J}	150	°C
Ambient temperature range	T_{A}	-40 85	°C
Storage temperature range	T_{STG}	-65 150	°C
ESD integrity HBM ²⁾	V_{ESD}	1	kV

¹⁾ All voltages refer to GND-Node.

²⁾ According to JESD22-A114



Electrical Characteristics

Thermal resistance

Table 3 Thermal resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}	240	K/W

¹⁾ For calculation of $R_{\rm thJA}$ please refer to Application Note Thermal Resistance

3 Electrical Characteristics

Table 4 DC Characteristics: $T_{\rm A}$ = 25 °C ; $V_{\rm CC}$ = 2.8 V, unless otherwise stated; no RF input signal

Parameter	Symbol		Values		Unit	Note / Test Condition
		Min.	Тур.	Max.		
Supply voltage	$V_{\sf CC}$	1.5		3.6	V	
Supply current high gain mode	I_{CCHG}		5.85		mA	
Supply current low gain mode	I_{CCLG}		0.55		mA	
Supply current at shutdown	I_{OFF}			5	μА	
Logic levels PON pin	V_{PON}	1.5		3.3	V	High
		0		0.4	V	Low
Current into PON pin	I_{PON}		25		μА	$V_{\rm Pon}$ = High, $V_{\rm GS}$ = Low
			35		μА	$V_{\rm Pon}$ = High, $V_{\rm GS}$ = High
			5		μА	$V_{\rm Pon}$ = Low, $V_{\rm GS}$ = High
				2	μА	$V_{\rm Pon}$ = Low, $V_{\rm GS}$ = Low
Logic levels GS pin	V_{GS}	1.5		3.3	V	High
		0		0.4	V	Low
Current into GS pin	I_{GS}		35		μΑ	$V_{\rm GS}$ = High
				2	μΑ	$V_{\rm GS}$ = Low



Electrical Characteristics

Table 5 Typical RF Characteristics 1) High-Gain Mode: $T_{\rm A}$ = 25 °C, $V_{\rm CC}$ = 2.8 V, $V_{\rm PON}$ = 2.8 V, $V_{\rm GS}$ = 0 V

Parameter	Symbol		Values			Note / Test Condition	
		Min.	Тур.	Max.			
Frequency Range	F_{BW}	170 ²⁾		1675	MHz	VHFIII/UHF/L-Band US/L-Band EU	
Power Gain	$ S_{21} $		15.75		dB	f = 470MHz	
Power Gain Variation over Frequency	$\Delta S_{21} $		1		dB	f = 170 MHz-1675 MHz	
Reverse Isolation	1/ S ₁₂		>25		dB		
Noise figure ³⁾	NF		1.3		dB	f = 470 MHz	
Input return loss	$1/ S_{11} $		>8		dB	50 Ω	
Output return loss	$1/ S_{22} $		>8		dB	50 Ω	
Stability factor ³⁾	k		>1.5			From 30 kHz to 6 GHz	
Input 1 dB compression point ³⁾ I	IP_{1dB}		-10		dBm	f = 170 MHz	
			-10		dBm	f = 470 MHz	
			-9		dBm	f = 1500 MHz	
3rd order input intercept point ³⁾	IIP_3		-7		dBm	f = 170 MHz; 1 MHz offset	
			-7		dBm	f = 470 MHz; 1 MHz offset	
			-3		dBm	f = 1500 MHz; 1 MHz offset	
Settling time for Power On ³⁾	t_{PON}		3.5		μs		
Settling time Power Off ³⁾	t_{POFF}		2		μs		

¹⁾ Measured on BGA728L7 application board without substracting PCB losses (unless noted otherwise) at 470 - 1675 MHz

^{2) 170} MHz to 240 MHz (VHF III) can be covered by adding external capacitor on input circuit (see Application Information)

³⁾ Verify by random sampling



Electrical Characteristics

Table 6 Typical RF Characteristics 1) Low-Gain Mode: $T_{\rm A}$ = 25 °C, $V_{\rm CC}$ = 2.8 V, $V_{\rm PON}$ = 2.8 V, $V_{\rm GS}$ = 2.8 V

Parameter	Symbol		Value	S	Unit	Note / Test Condition
		Min.	Тур.	Max.		
Frequency Range	F_{PW}	170 ²⁾		1675	MHz	VHFIII/UHF/L-Band US/L-Band EU
Power Gain	$ S_{21} $		-5.2		dB	
Power Gain Variation over Frequency	$\Delta S_{21} $		2.1		dB	f = 170 MHz-1675 MHz
Noise figure ³⁾	NF		5.5		dB	f = 470 MHz
Input return loss	$I/ S_{11} $		>8		dB	50 Ω
Output return loss	1/ S ₂₂		>8		dB	50 Ω
Input compression point ³⁾	IP_{1dB}		3		dBm	f = 170 MHz
			3.5		dBm	f = 470 MHz
			5		dBm	f = 1500 MHz
3rd order input intercept point ³⁾	IIP_3		16		dBm	f = 170 MHz; 1 MHz offset
			16		dBm	f = 470 MHz; 1 MHz offset
			20		dBm	f = 1500 MHz; 1 MHz offset
Settling time GS ON ³⁾	t_{GSON}		2		μs	
Settling time GS OFF ³⁾	t_{GSOFF}		3.5		μs	

¹⁾ Measured on BGA728L7 application board including PCB losses (unless noted otherwise) at 470 - 1675 MHz

Gain Mode Selection Truth Table

Control Voltage V_{PON}^{-1}	Control Voltage $V_{\rm GS}^{-1}$	Gain Mode
High	Low	High Gain
High	High	Low Gain
Low	High	Low Gain
Low	Low	OFF

¹⁾ See Table 4 for the High/Low voltage range

^{2) 170} MHz to 240 MHz (VHF III) can be covered by adding external capacitor on input circuit (see Application Information)

³⁾ Verify by random sampling



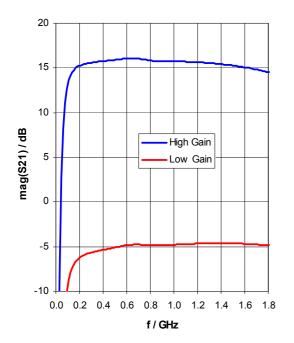
Typical Measured Results

4 Typical Measured Results

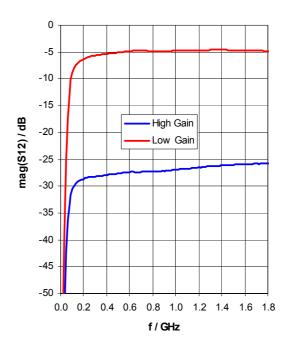
 $T_{\rm A}$ = 25 °C, $V_{\rm CC}$ = 2.8 \lor , $V_{\rm PON}$ = 2.8 \lor , $V_{\rm GS}$ = 0 \lor for High Gain Mode, $V_{\rm GS}$ = 2.8 \lor for Low Gain Mode Note: Measurements based on VHF-board application. For UHF application NF can be further optimized by omitting the optional capacitor C5.

Note: Board losses are not substracted

Gain
$$|S_{21}| = f(f)$$



Isolation $|S_{12}| = f(f)$

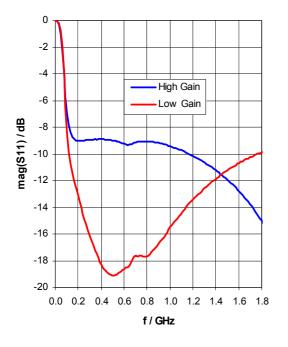


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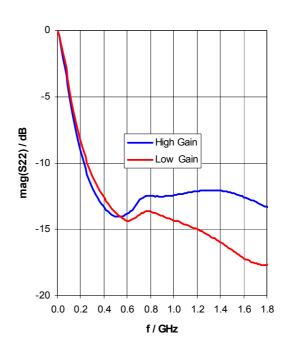


Typical Measured Results

Input Return Loss $|S_{11}| = f(f)$

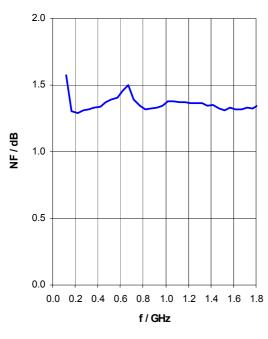


Output Return Loss $|S_{22}|$ = f (f)

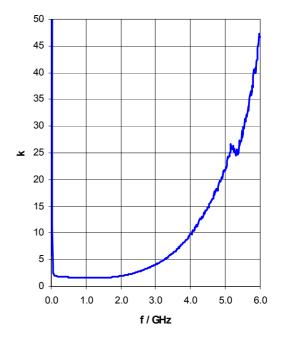


IRLvsd ORL.vsd

High Gain Noise Figure NF = f(f)



High Gain Stability Factor k = f(f)



NF.vsd K_factor.vsd



Application Information

5 Application Information

Application Circuit

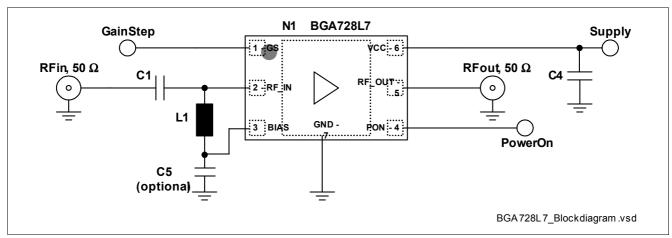


Figure 2 Application circuit of BGA728L7

Table 7 Bill of Materials

Name	Value	Package	Manufacturer	Function
C1	56 pF	0402	Various	DC block
C4	1 nF	0402	Various	Supply voltage filtering
C5	1 nF	0402	Various	Optional for VHF-band
L1	75 nH	0402	Murata LQW15AN75NG00	Bias Feed
N1	BGA728L7	TSLP-7-1	Infineon	SiGe LNA
C2, C3	not used			

A list of all application notes including AN163 in particular for BGA728L7 is available at http://www.infineon.com/MobileTVLNA

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Application Information

Application Board

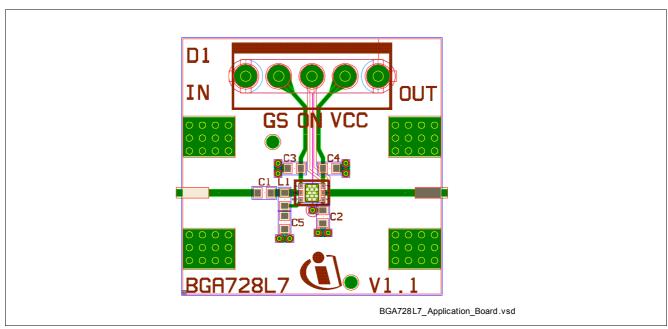


Figure 3 Application Board

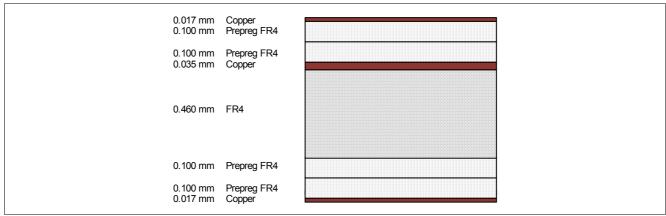


Figure 4 Cross section View of Application board

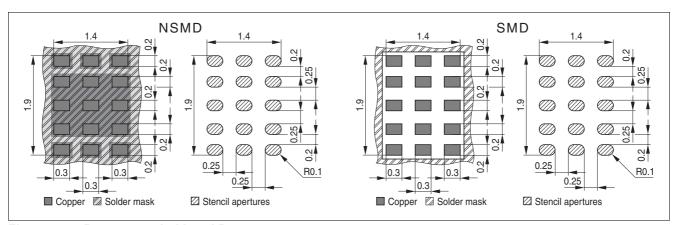


Figure 5 Recommended Land Pattern



Package Information

6 Package Information

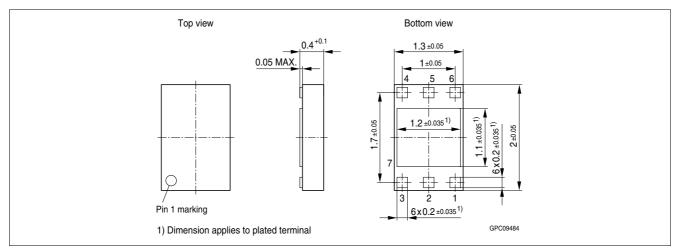


Figure 6 Package Dimensions for TSLP-7-1

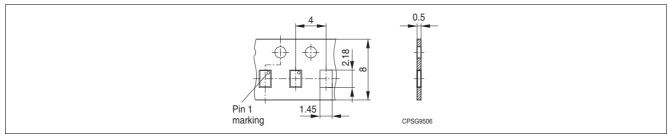


Figure 7 Tape & Reel Dimensions (Ø reel 180, pieces/reel 7500)

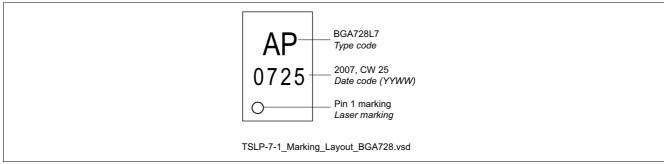


Figure 8 Marking Layout